

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A large-diameter SiC wafer, wherein a diameter is increased as a double structure of single crystal SiC and polycrystal SiC by planarly forming a film of polycrystal SiC in a flat plate shape in which a polycrystal SiC is grown up to be in a size, which corresponds to a handling device of an existing semiconductor manufacturing line, around an outer circumference of a small diameter α -SiC single crystal wafer previously formed as a wafer.

2. (Currently Amended) The large-diameter SiC wafer according to claim 1, wherein at least two or more of said small-diameter α -SiC single crystal wafers are placed on a graphite plate.

3. (Original) The The large-diameter SiC wafer according to claim 1, wherein said polycrystal SiC is a β -SiC manufactured by a CVD method.

4. (Canceled)

5. (Currently Amended) A manufacturing method of a large-diameter SiC wafer comprising the steps of: planarly placing-growing polycrystal SiC from at least one surface side of a small diameter α -SiC single crystal wafer previously formed as a wafer on a graphite plate and simultaneously masking a surface of a substrate; planarly forming a film of so as to be in a size of an outer diameter corresponding to a handling device of an existing semiconductor manufacturing line; polycrystal SiC around an outer circumference of said wafer from its masking plane side and integrating them; and thereafter grinding the polycrystal SiC on the surface of the α -SiC single crystal wafer to manufacture an increased-diameter SiC of a double structure in which the polycrystal SiC plate portion is formed-is grown around an outer circumference of the small-diameter α -SiC single crystal wafer.